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(71) Applicant(s):

MITSUBISHI ELECTRIC CORPORATION [JP/JP]; 7-3, Marunouchi 2-chome, Chiyoda-ku, Tokyo 1008310 (JP) (*for all designated states*)

(72) Inventor(s):

YAMAGUCHI, Yutaro; c/o Mitsubishi Electric Corporation, 7-3, Marunouchi 2-chome, Chiyoda-ku, Tokyo 1008310 (JP)

OTSUKA, Tomohiro; c/o Mitsubishi Electric Corporation, 7-3, Marunouchi 2-chome, Chiyoda-ku, Tokyo 1008310 (JP)

HANGAI, Masatake; c/o Mitsubishi Electric Corporation, 7-3, Marunouchi 2-chome, Chiyoda-ku, Tokyo 1008310 (JP)

SHINJO, Shintaro; c/o Mitsubishi Electric Corporation, 7-3, Marunouchi 2-chome, Chiyoda-ku, Tokyo 1008310 (JP)

(74) Agent(s):

TAZAWA, Hideaki; Akasaka Sanno Center Bldg. 5F, 12-4, Nagata-cho 2-chome, Chiyoda-ku, Tokyo 1000014 (JP)

(54) Title (EN): SEMICONDUCTOR DEVICE

(54) Title (FR): DISPOSITIF À SEMI-CONDUCTEUR

(54) Title (JA): 半導体装置

(57) Abstract:

(EN): A semiconductor device comprising a plurality of gate fingers (2-1 - 2-8) extending symmetrically from both sides of a gate connection part (2a-1 - 2a-3), a drain electrode (3-1, 3-2) adjacent to both of the gate fingers (2-1 - 2-8) extending from both sides of the gate connection part (2a-1 - 2a-3), and a plurality of source electrodes (4-1 - 4-6) adjacent to the gate fingers (2-1 - 2-8) extending from both sides of the gate connection part (2a-1 - 2a-3), wherein a gate air bridge (8-1 - 8-3) connects the gate connection part (2a-1 - 2a-3) to a gate routing line (6) over a source electrode (4-2, 4-4, 4-6).

(FR): La présente invention porte sur un dispositif à semi-conducteur comprenant une pluralité de doigts de grille (2-1 - 2-8) partant symétriquement des deux côtés d'une partie de connexion de grille (2a-1 - 2a3), une électrode drain (3-1, 3-2) adjacente aux deux doigts de grille (2-1 - 2-8) partant des deux côtés de la partie de connexion de grille (2a-1 - 2a3), et une pluralité d'électrodes source (4-1 - 4-6) adjacentes aux doigts de grille (2-1 - 2-8) partant des deux côtés de la partie de connexion de grille (2a-1 - 2a3), un pont aérien de grille (8-1 - 8-3) connectant la partie de connexion de grille (2a-1 - 2a3) à une ligne de routage de grille (6) au-dessus d'une électrode source (4-2, 4-4, 4-6).

(JA): ゲート接続部(2 a - 1 ~ 2 a - 3)の両側から対称的に延びた複数のゲートフィンガー(2 - 1 ~ 2 - 8)と、ゲート接続部(2 a - 1 ~ 2 a - 3)の両側から延びたゲートフィンガー(2 - 1 ~ 2 - 8)の両方に隣接しているドレイン電極(3 - 1, 3 - 2)と、ゲート接続部(2 a - 1 ~ 2 a - 3)の両側から延びたゲートフィンガー(2 - 1 ~ 2 - 8)に個々に隣接している複数のソース電極(4 - 1 ~ 4 - 6)とを備え、ゲートエアブリッジ(8 - 1 ~ 8 - 3)が、ソース電極(4 - 2, 4 - 4, 4 - 6)を跨いでゲート接続部(2 a - 1 ~ 2 a - 3)とゲート引き回し線路(6)とを接続している。

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